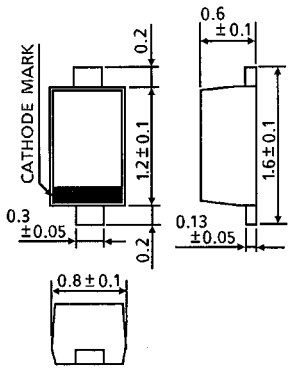
TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1SV314

VCO FOR UHF BAND RADIO

- High Capacitance Ratio : $C_{0.5\ V} / C_{2.5\ V} = 2.5$ (Typ.)
- Low Series Resistance : $r_s = 0.35\ \Omega$ (Typ.)
- Useful for Small Size Tuner

Unit: mm



ESC

JEDEC	—
EIAJ	—
TOSHIBA	1−1G1A

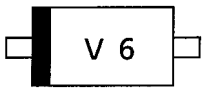
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Reverse Voltage	V_R	I_R = 1μA	10	—	—	V
Reverse Current	I_R	V_R = 10 V	—	—	3	nA
Capacitance	$C_{0.5\ V}$	V_R = 0.5 V, f = 1 MHz	7.3	—	8.4	pF
Capacitance	$C_{2.5\ V}$	V_R = 2.5 V, f = 1 MHz	2.75	—	3.4	pF
Capacitance Ratio	$\frac{C_{0.5\ V}}{C_{2.5\ V}}$	—	2.4	2.5	—	—
Series Resistance	r_s	V_R = 1 V, f = 470 MHz	—	0.35	0.45	Ω

MARKING



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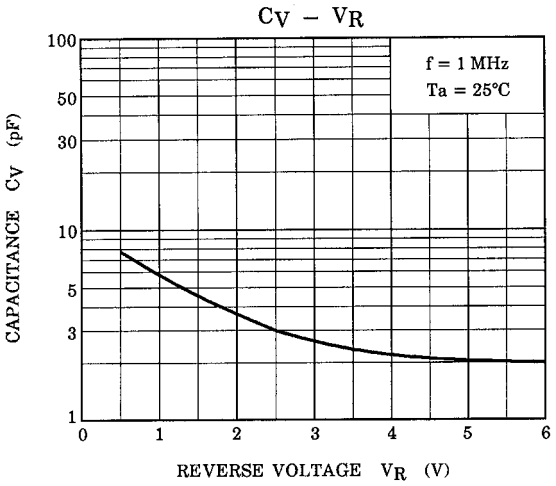

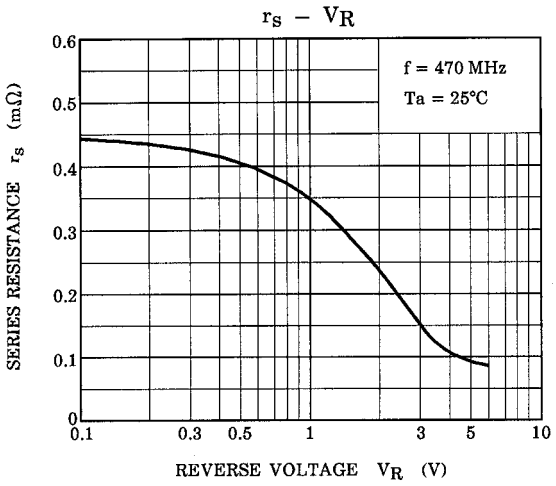

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